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Hasegawa et al.

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(54) **POWER SEMICONDUCTOR DEVICE**

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(**) Term: **15 Years**

(21) Appl. No.: **29/568,592**

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Related U.S. Application Data

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(30) **Foreign Application Priority Data**

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Apr. 2, 2014	(JP)	2014-007264
Apr. 2, 2014	(JP)	2014-007265
Apr. 2, 2014	(JP)	2014-007266

(51) **LOC (10) Cl.** **13-03**

(52) **U.S. Cl.**
USPC **D13/182**

(58) **Field of Classification Search**
USPC D13/182
CPC H01L 21/00; H01L 21/02433; H01L 2224/42; H01L 2224/43; H01L 2021/00; H01L 2021/02; H01L 2021/04; H01L 21/4814; H01L 21/4846; H01L 21/4871; H01L 21/67144; H01L 23/12; H01L 23/13; H01L 23/14; H01L 23/147; H01L 2924/171; H01L 2924/1711; H01L 2924/1715; H01L 2924/17151; H01L 2924/181; H01L 2924/1811; H01L 2924/1815; H01L 2924/19042; H01L 2924/1905; H01L 2224/08054; H01L 23/58; H05B 41/14; H02B 6/4201; G02B 6/4256; G02B 6/4257; G02B 6/4261; G02B 6/4262; G02B 6/42; G02B 6/4281; H05K 1/14; H05K 1/141; H05K 1/142; H05K 1/144; H05K 1/18; H05K 1/181; H05K 1/182; H05K 1/026; H05K 1/0228; H05K 1/0245; H05K 1/0236; H05K 1/0263
See application file for complete search history.

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(57) **CLAIM**

The ornamental design for a power semiconductor device, as shown and described.

DESCRIPTION

FIG. **1** is a front, right side, bottom perspective view of a power semiconductor device showing our new design;
FIG. **2** is a rear, left side, top perspective view thereof;
FIG. **3** is a front view thereof;
FIG. **4** is a rear view thereof;
FIG. **5** is a left side view thereof;
FIG. **6** is a right side view thereof;
FIG. **7** is a top plan view thereof; and,
FIG. **8** is a bottom plan view thereof. The broken lines shown represent unclaimed subject matter of a power semiconductor device and form no part of the claimed design.

1 Claim, 8 Drawing Sheets

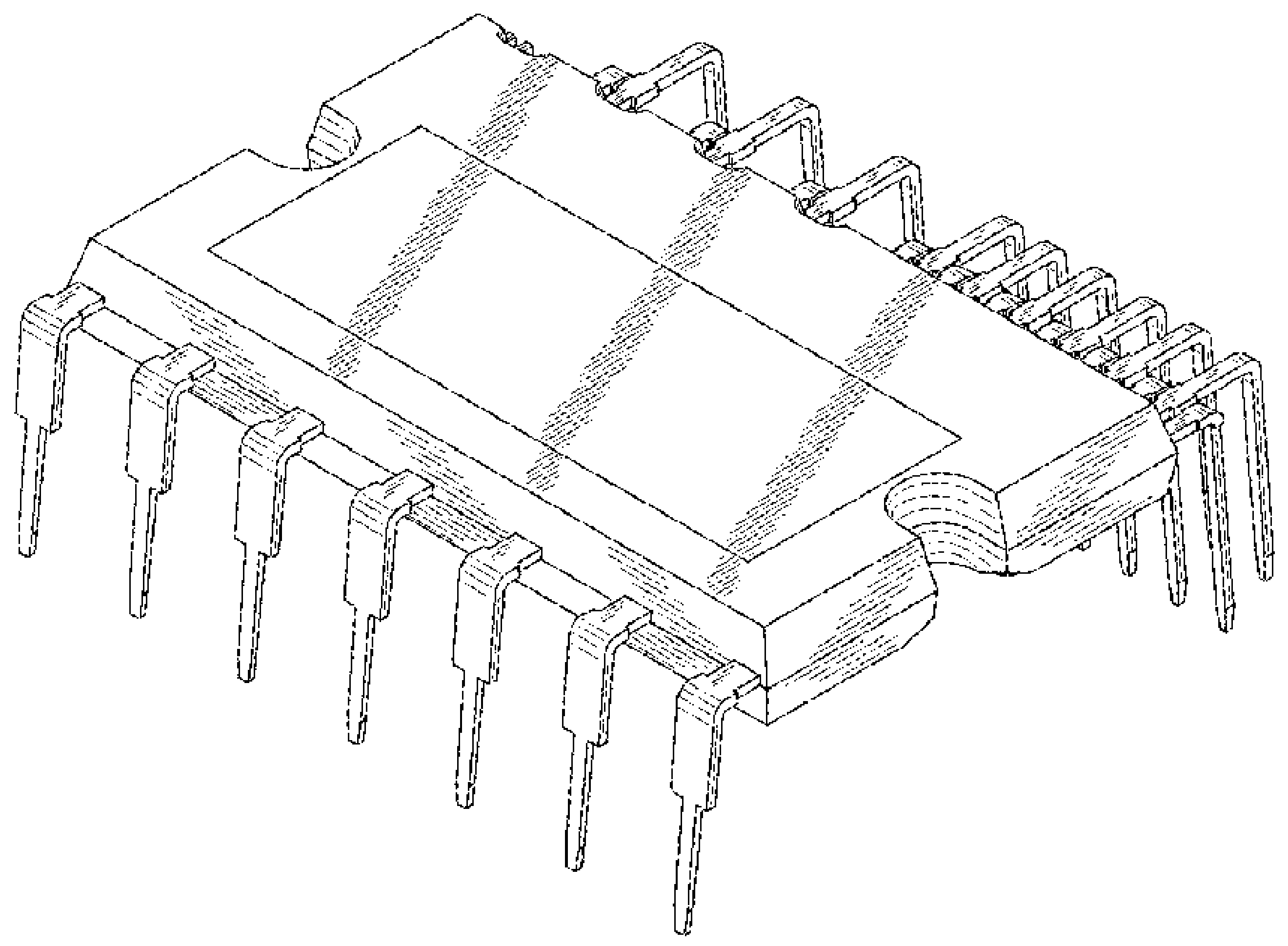

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FIG. 1

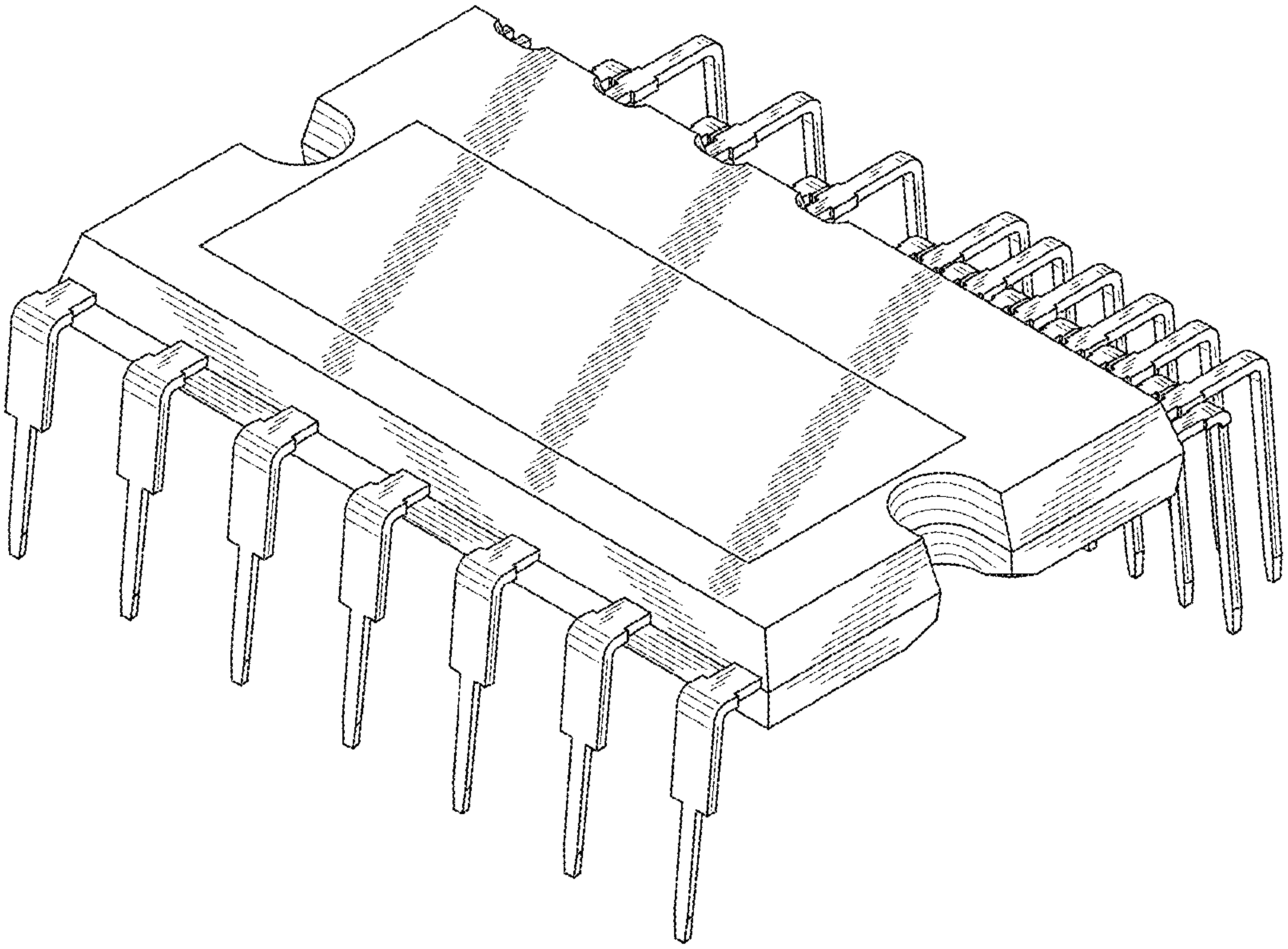

FIG. 2

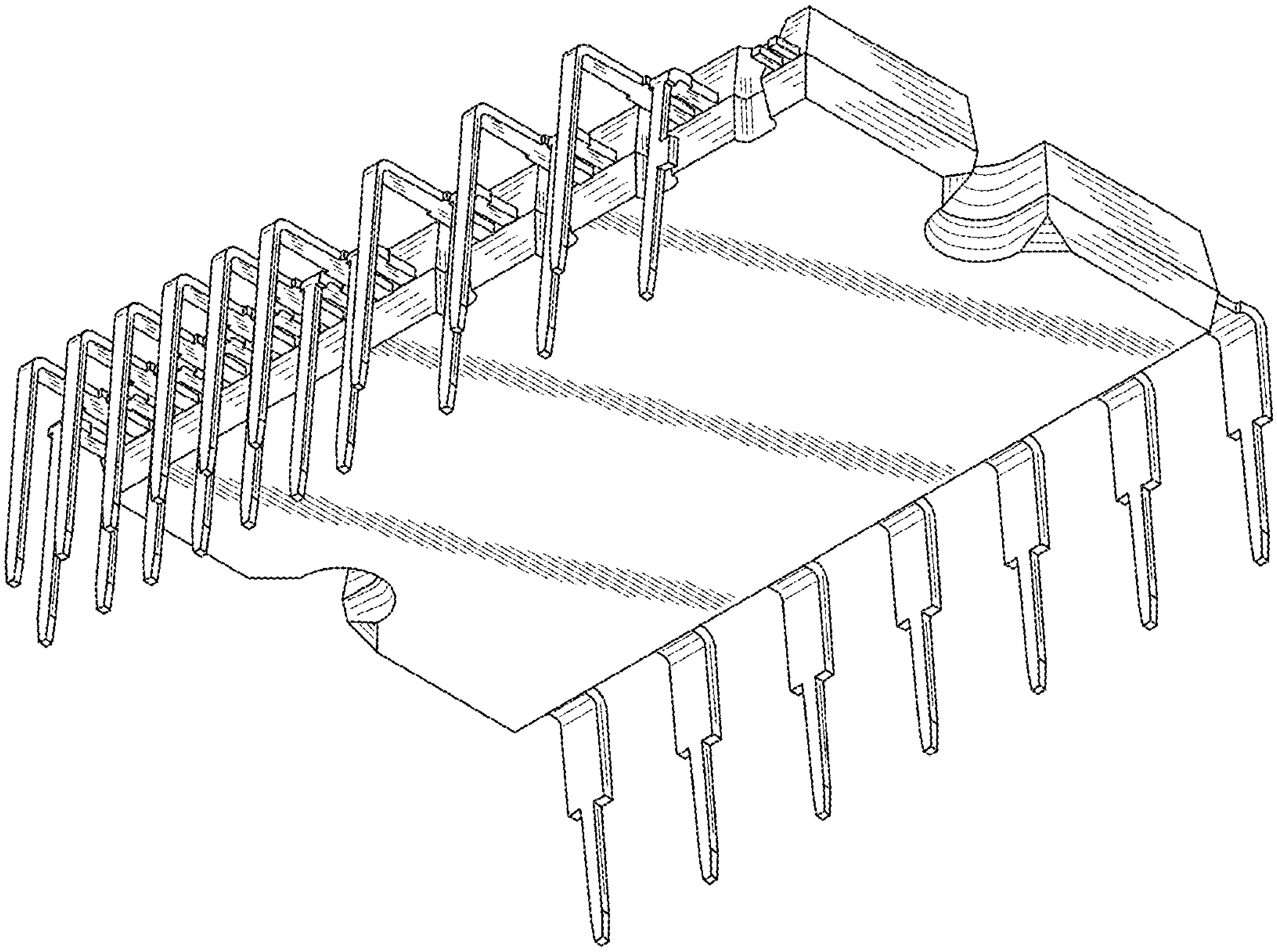

FIG. 3

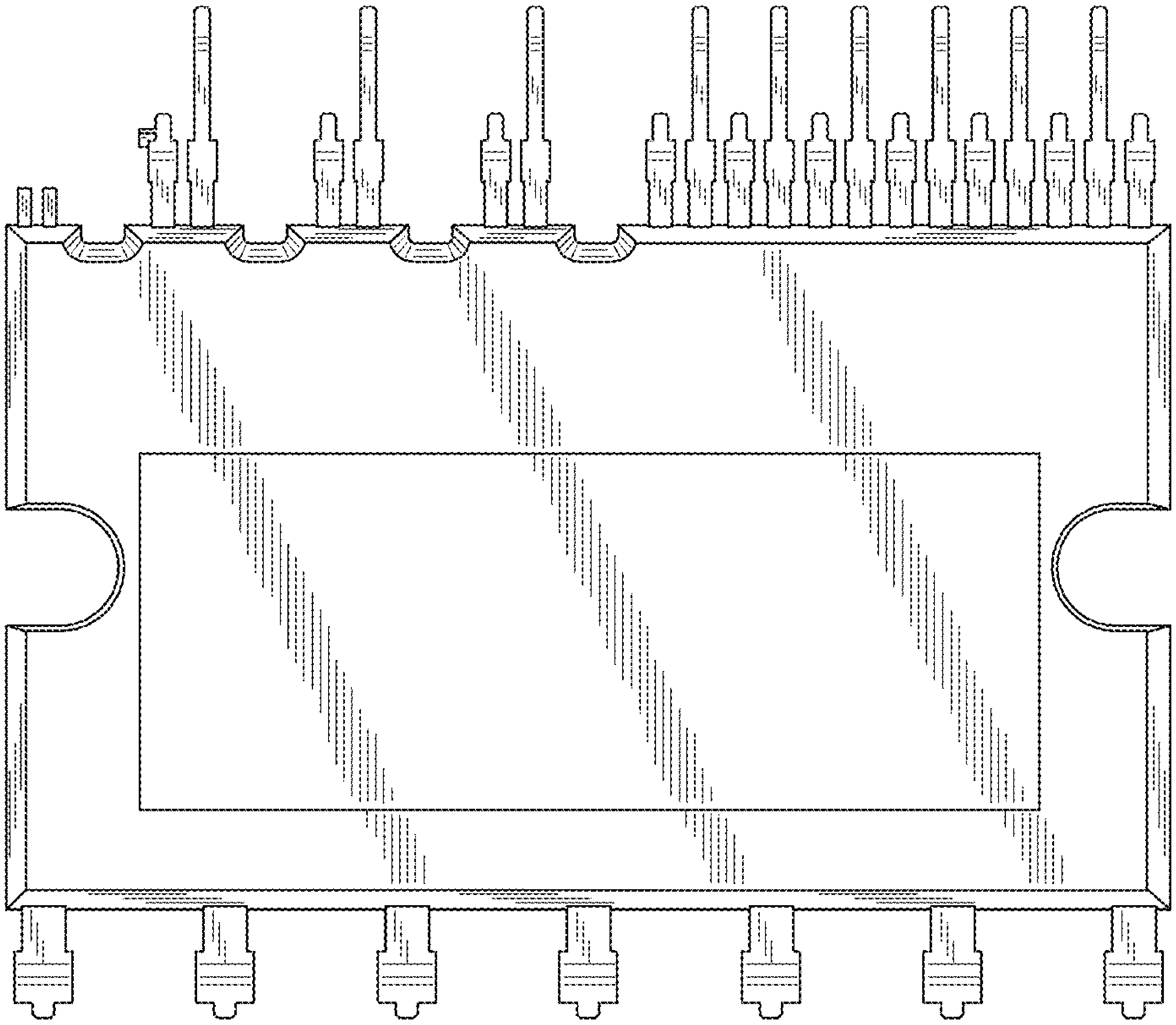

FIG. 4

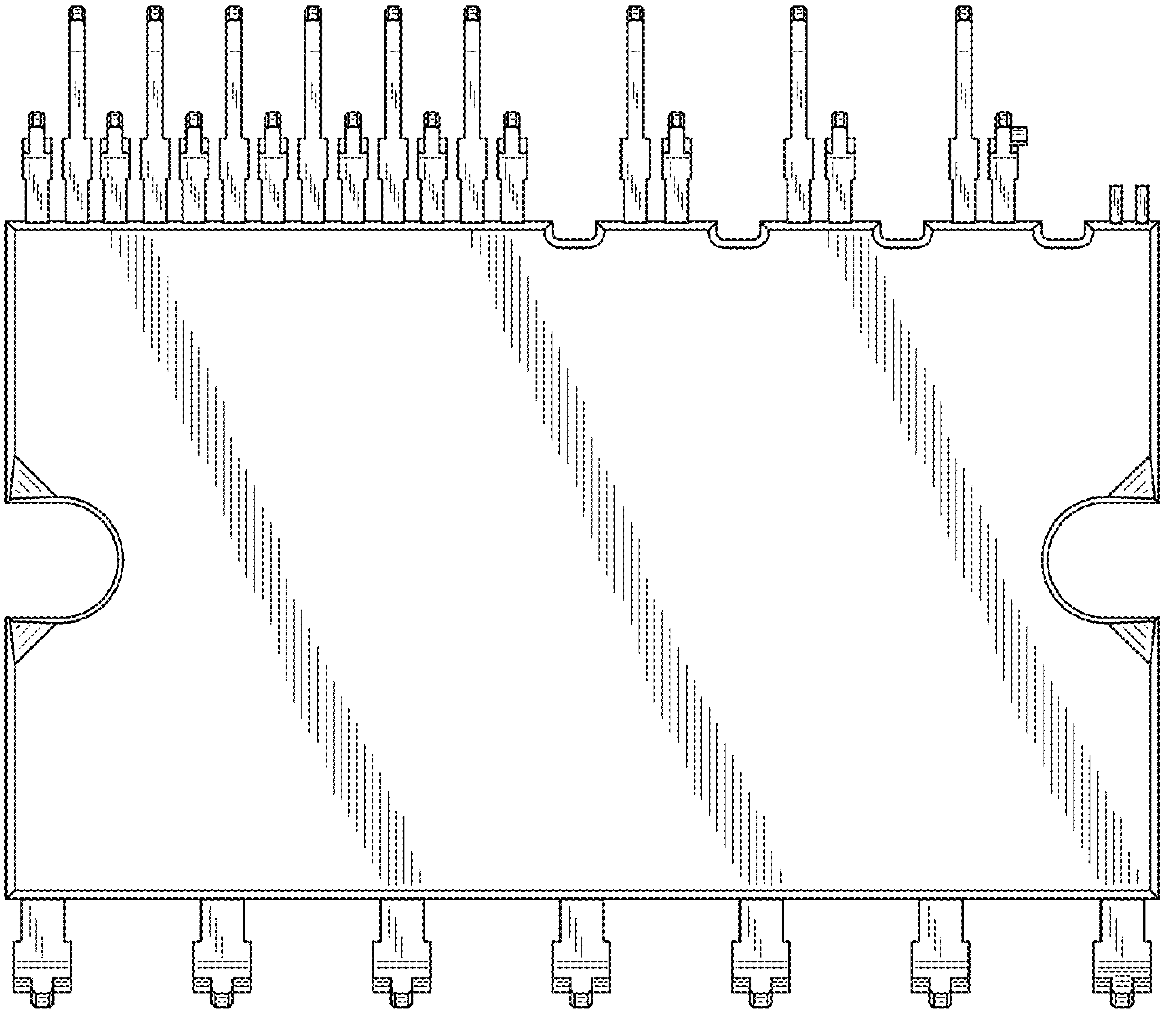

FIG. 5

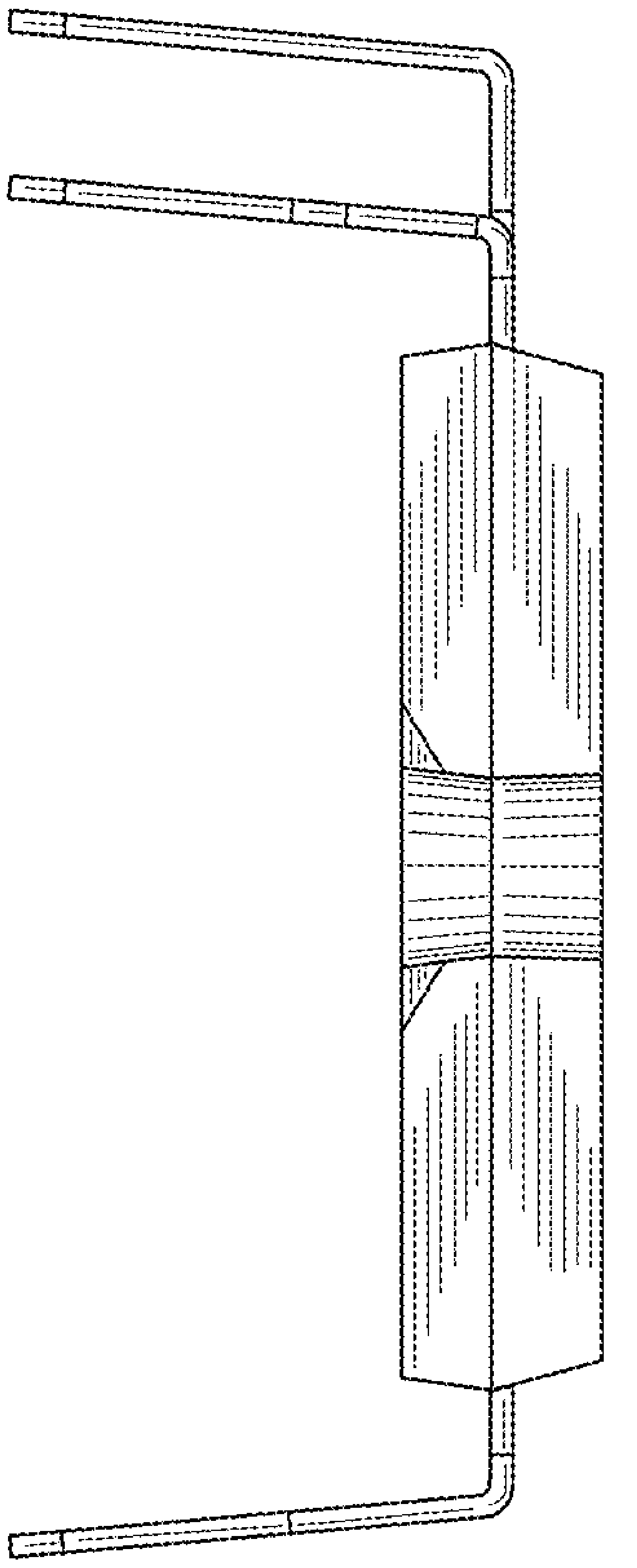

FIG. 6

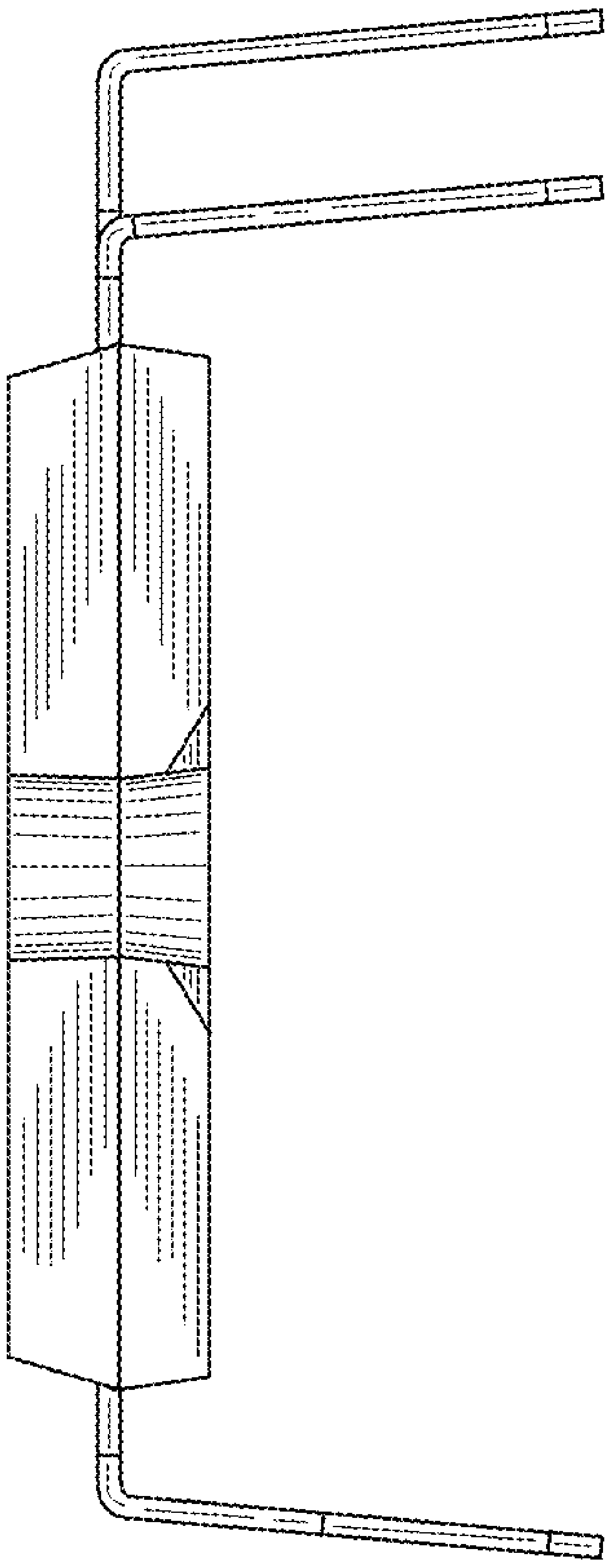

FIG. 7

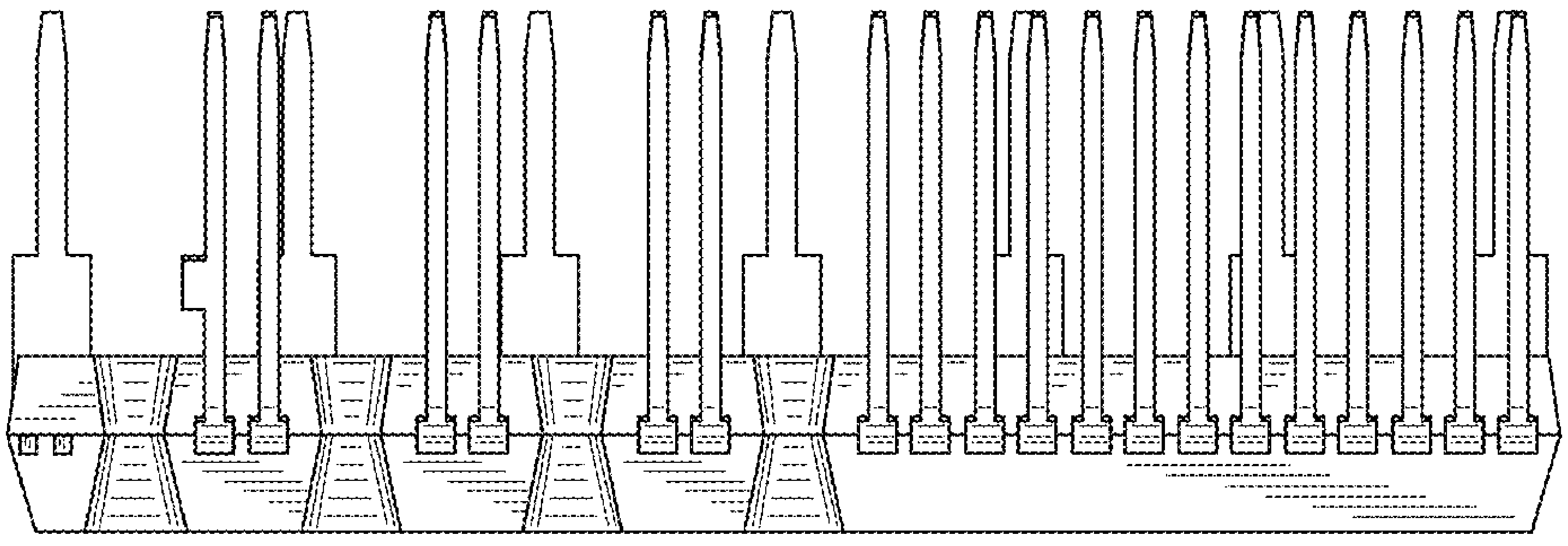

FIG. 8